Report No: NSWC C6054-2N5114-0001

Program: NASA GODDARD			Report Date: 1/31/2002		
Generic Part No. Part Description: Manufacturer:					
2N5114	40-V, 100-Ohm P-Channel FET	Solitron			
Package Type:	Package Markings	Package Markings			
TO-18	9518	JV2N5114CDCD USA 9518 X02546			
Detailed Test Specification:	General Test Requirement:	Performance Specification			
2N5114 TID Test Plan	2N5114 TID Test Plan		MIL-PRF-19500/476B		
Serial Number:		Radiation Test Results			
1, 2, 3, 4, 5, 6, 7, 8, 9, & 10 (manually marked)		See Appendix B, C, D, and E			

1.0 Summary.

NAVSEA Crane was tasked to evaluate the total ionizing dose (TID) performance of this P-channel 40-V, 100-Ohm JFET (2N5114) to conditions specified by Christian Poivey, NASA-GSFC, Code 561, Greenbelt MD 20771. Prior to the test, Jeff Titus (NAVSEA) contacted Christian Poivey about the selected bias conditions. After some discussion via emails, the TID Test Plan was modified to the following TID conditions:

Revised 2N5114 TID Test Plan (12/28/2001)

Bias Condition	# of Test Samples	Drain	Gate	Source
1	3	5 V	0 V	5 V
2	3	0 V	5 V	0 V
3	2	0 V	0 V	0 V

NAVSEA Crane was tasked to perform these tests:

a.) Electrical Measurements (I_{GSS}, I_{DSOFF}, R_{DSON}, and V_{GSOFF}), Gamma irradiations at dose levels of 2.5, 5, 10, 20, 30, and 50 krd(Si) using a dose rate less than 1 rd(Si)/s repeating electrical measurement after achieving the specified dose levels, and finally a Post-Radiation anneal test for 168 hrs @ 25°C with electrical measurements, afterwards. The actual anneal time was modified and electrical measurements were performed after 156 hours and a total of 210 hours instead of 168 hours.

Test results indicate that only IDSS and IGSS were sensitive to total ionizing dose effects at levels up to 50 krad(Si). Both of these parameters exceeded their specification limit at 50 krad(Si). The bias condition that produced the largest change was VD=VS=VG=0 volts. IDSS increased from 5.2 to 555 pA at 50 krad(Si) and to 584 pA after anneal. IGSS increased from 8.5 to 994 pA at 50 krad(Si) and to 1080 pA after anneal. RDS_ON slightly increased from 60 to 62 ohms at 50 krad(Si) and after anneal. VGS_OFF increased from 7.70 to 7.75 volts at 50 krads(Si) and to 7.85 V after anneal. Detailed radiation data are provided in Appendix B, C, D, while graphical plots are provided in Appendix E.

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2.0 Applicable Documents.00

The major applicable documents, used to perform the TID tests, are listed here:

a.) 2N5114 TID TEST PLAN NASA Supplied TID Test Plan

b.) 2N5114 TID TP REVISED
 c.) MIL-PRF-19500/476B
 d.) MIL-STD-750D
 Method 1019.4
 Modified Test plan via email communications
 Performance Specification P-Channel JFET
 Test Methods for Semiconductor Devices
 Steady State Total Dose Irradiation Procedure

Method 3400 Conditions for Measurement of MOS FET Parameters

3411.1 Gate Reverse Current (IG_OFF) 3415.1 Drain Reverse Current (ID_OFF)

3421.1 Static Drain to Source On Resistance (RDS_ON)

3403.1 Gate to source Voltage (VGS_OFF)

e.) ASTM Standard E668 Standard Practice for the Application of Thermoluninscensce

Dosimetry (TLD) Systems for Determining Absorbed Dose in Radiation Hardness Testing of Electronic Devices - Annual Book of ASTM Standards, Vol. 12.02: Nuclear (II), Solar, and Geothermal

Energy, American Society for Testing and Materials

f.) NAVSEA INST 4734.1 NAVSEA Metrology and Calibration Program

g.) DOD-HDBK-263 Handbook - Electrostatic discharge sensitive devices

3.0 Handling Precautions.

Handling precautions were observed to minimize electrostatic discharge (ESD).

4.0 Electrical Test.

Electrical measurements were performed using either a Model Tektronix 370 curver tracer and/or an automated test system consisting of two Keithley 0237s and a controller. Two controls along with the 8 test samples were individually measured and recorded. The specified electrical tests are:

PARAMETER	CONDITION	PARAMETER	LIMIT
Gate Reverse Current	$V_{DS} = 0 V;$	${ m I}_{ m GS_OFF}$	< 500 pA
$({ m I}_{ m GS_OFF})$	$V_{GS} = 20 \text{ V}$		
Drain Current Cutoff	$V_{DS} = -15 \text{ V};$	$I_{ m DS_OFF}$	< -500 pA
$(\mathrm{I}_{\mathrm{GS_OFF}})$	$V_{GS} = 12 \text{ V}$		
Drain-Source On	$I_{DS} = -1 \text{ mA};$	$R_{ m DS_ON}$	75 Ohm
Resistance (R _{DS_ON})	$V_{GS} = 12 \text{ V}$		
Gate Source Cutoff	$I_{DS} = -1 \text{ nA};$	$ m V_{GS_OFF}$	< 10 V
(V_{GS_OFF})	$V_{DS} = -15 \text{ V}$		

Note: Appendix A provides a summary of a visual inspection of the test samples.

Appendix B provides a summary of the initial pre-radiation electrical test measurements.

Appendix C provides a summary of the post-radiation electrical test measurements.

Appendix D provides a summary of post-anneal electrical test measurements.

Appendix E provides graphical responses of electrical test parameters.

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4.1 Test Conditions.

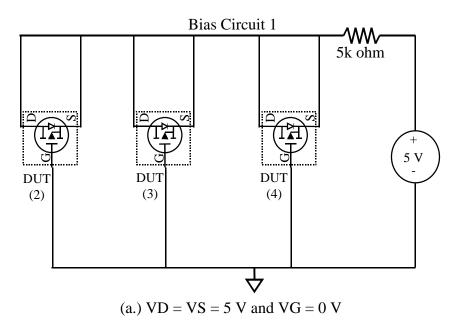
Test conditions were performed as specified by the applicable documents of 2.0 (specifically, the 2N5114 TID Test Plan Revised). All electrical measurements were performed at an ambient room temperature of $22 \,^{\circ}\text{C} \pm 3 \,^{\circ}\text{C}$ and recorded prior to and after electrical tests.

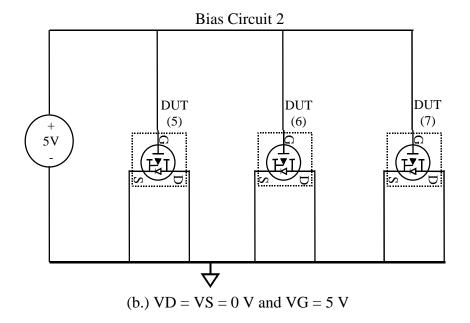
5.0 Total Ionizing Dose (TID) Test.

Total ionizing dose tests were performed at the NAVSEA Crane Co-60 test facility using a J. L. Shepherd and Associates Model 81-22 Irradiator with a Model 484 Radiation Tunnel and Interlock Door Assembly. Test samples were placed inside a Pb/Al container to minimize dose enhancement effects caused by low-energy scattering. The desired dose rate is achieved by selecting different amounts of radioactivity and distance. For this test, the 8,000 curies source was used with the positioning table set at 670 mm.

5.1 Bias Circuit.

A custom bias board was designed and fabricated to perform the TID tests. The bias circuit conformed to the requirements of the test specification (see bias conditions - NASA 2N5114 TID Test Plan and Test Plan modifications of Summary, Section 1). Figure 1a depicts the TID insitu bias circuit used for three of the eight test samples ($V_D = V_S = 5 \text{ V}$ and $V_G = 0 \text{ V}$). Since the gated pn junction is hard on, the 5 k Ω resistor was employed to limit the overall gate current to 1 mA. Figure 1b depicts the TID bias circuit used for the other three samples ($V_D = V_S = 0 \text{ V}$ and $V_G = 5 \text{ V}$). The other two samples were biased with all leads common ($V_D = V_S = V_G = 0V$) as depicted in Figure 1c. This bias (all pins grounded) was found to produce the largest change in IDSS and IGSS. Figure 2 shows a pictorial representation of the of the TID bias board. Note that all eight test samples were exposed simultaneously.





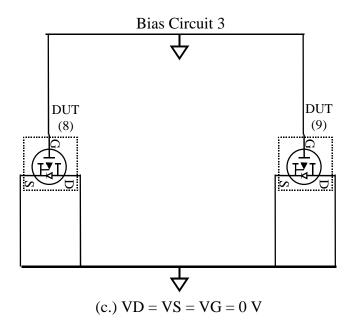


Figure 1. Bias circuits used in TID test.

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Top of Board P-Channel JFET TID Board

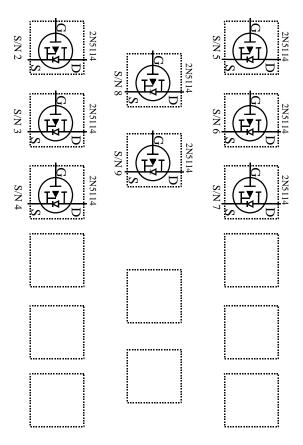


Figure 2. TID board layout of bias circuitry.

5.2 Dosimetry.

The dosimetry standard used is described in 2.0(e).

For total dose dosimetry, three ribbons were placed in a TLD holder and wrapped in a thin, (~0.001 inches) aluminum foil. The average reading of these three ribbons is used to determine the dose rate of the Co-60 source. For this test, TLDs were placed upon the top left socket, top right socket, bottom left socket, bottom right socket and the middle of all the sockets as depicted in Figure 3. Note, this dosimetry was used to determine exposure times for all tests performed. Table 2 provides a summary of the Co-60 Gamma Cell 220 source dosimetry.

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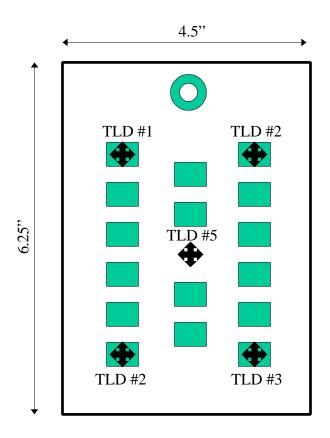


Figure 3. Pictorial Representation Showing TLD Placement.

TLD	Slide	Avg. Dose	Standard	Dose Rate	Board
Package	Number	Rd(CaF2)	Deviation	[Rd(Si)/s]	Position
1	101	123.5	2.9%	0.8948	Top Left
2	102	124.2	0.6%	0.9000	Top Right
3	103	127.4	3.8%	0.9228	Bottom Left
4	104	119.7	1.4%	0.8677	Bottom Right
5	105	123.4	2.6%	0.8942	Middle
6	106	2489	1.6%	0.8861	Top Right

Table 2. Verification of Co-60 Source

Based upon the dosimetry, the dose rate was determined to be $0.89 \, \text{rd}(\text{Si})/\text{s}$. To validate the first radiation level (and to verify the dose rate), another TLD (top right corner) was placed upon the TID board above the top right socket. The exposure time was set for 2809 seconds (0.89 x 2,809 = 2,500), resulting in an average TLD reading of 2,489 rd(Si).

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Table 3 is a summary of the required exposure times to achieve radiation levels of 2.5, 5, 10, 20, 30, and 50 krd(Si) as required by the 2N5114 TID Test Plan. Table 3 also provides the times to perform the electrical measurements between each exposure.

Table 3. Summary of Exposure and Electrical Test Times of TID Test

Total Dose	Exposure	Exposure	Total Dose	Electrical Test	Electrical Test
Test Date	Start Time	Stop Time	Rd(Si)	Start Time	Stop Time
01/18/2001	9:42 AM	10:29 AM	2,500	10:31 AM	11:02 AM
01/18/2001	11:04 AM	11:51 AM	5,000	11:53 AM	12:06 PM
01/18/2001	12:09 PM	1:43 PM	10,000	1:44 PM	1:57 PM
01/18/2001	1:59 PM	5:07 PM	20,000	5:09 PM	5:27 PM
01/18/2001	5:29 PM	8:36 PM	30,000	8:37 PM	8:49 PM
01/18/2001	8:51 PM	3:06 AM	50,000	3:08 AM	3:23 AM

5.3 Post-Radiation Anneal Test.

Upon completion of the last exposure (50 krd(Si)) and electrical characterization, samples were annealed for 156 hours at 25 °C under similar bias conditions. After annealing, the samples were electrically characterized again. After electrical characterization, samples were annealed for an additional 54 hours at 25 °C and electrically characterized again. This slight modification was performed to accommodate test personnel and the unusual test schedule (168 hr anneal would have required electrical test be conducted at 3:23 AM on a Saturday).

APPENDIX A. Visual Inspection Summary

Tagged S/N	Package Markings	Marking Verified	Comments
001	JV2N5114CDCD	Yes	
	USA 9518 X02546		
002	JV2N5114CDCD	Yes	
	USA 9518 X02546		
003	JV2N5114CDCD	Yes	
	USA 9518 X02546		
004	JV2N5114CDCD	Yes	
	USA 9518 X02546		
005	JV2N5114CDCD	Yes	
	USA 9518 X02546		
006	JV2N5114CDCD	Yes	
	USA 9518 X02546		
007	JV2N5114CDCD	Yes	
	USA 9518 X02546		
008	JV2N5114CDCD	Yes	
	USA 9518 X02546		
009	JV2N5114CDCD	Yes	
	USA 9518 X02546		
010	JV2N5114CDCD	Yes	
	USA 9518 X02546		

Note: Samples were received without assigned S/Ns. S/Ns were randomly assigned by NAVSEA and printed on the case using a permanent marker.

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Appendix B. Summary of Initial Electrical Test Data

S/N	I_{GS-OFF}	I _{DS_OFF}	R _{DS_ON}	$ m V_{GS_OFF}$	V_{GS_OFF}	Allocated
	$V_{DS} = 0 V;$	$V_{DS} = -15 \text{ V};$	$I_{DS} = -1 \text{ mA};$	$I_{DS} = 1 \text{ mA}$	$I_{DS} = 1 \text{ nA}$	Test
	$V_{GS} = 20 \text{ V}$	$V_{GS} = 12 \text{ V}$	$V_{GS} = 0 V$	$V_{DS} = -15 \text{ V};$	$V_{DS} = -15 \text{ V};$	
001	8.22E-12	-4.86E-12	53	5.70	6.90	Control
002	1.03E-11	-6.47E-12	58	4.70	5.70	Bias 1
003	1.04E-11	-6.38E-12	58	4.70	6.50	Bias 1
004	9.40E-12	-5.76E-12	58	4.90	6.10	Bias 1
005	9.51E-12	-6.02E-12	60	4.60	5.90	Bias 2
006	8.75E-12	-5.36E-12	58	5.00	6.30	Bias 2
007	8.96E-12	-5.37E-12	58	4.70	5.90	Bias 2
800	1.03E-11	-6.22E-12	50	6.50	7.70	Bias 3
009	8.49E-12	-5.15E-12	54	5.70	7.10	Bias 3
010	8.15E-12	-4.90E-12	60	4.70	5.80	Control

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010

6.58E-12

-3.92E-12

Appendix C. Summar	v of Electrical Parameters .	After each Radiation Level
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	Appen	dix C. Summary of	f Electrical Param	eters After each R	adiation Level	
		R	adiation Level 2,5	00 rd(Si)		
S/N	I_{GS-OFF} $V_{DS} = 0 \text{ V};$ $V_{GS} = 20 \text{ V}$	I_{DS_OFF} $V_{DS} = -15 \text{ V};$ $V_{GS} = 12 \text{ V}$	R_{DS_ON} $I_{DS} = -1 \text{ mA};$ $V_{GS} = 0 \text{ V}$	V_{GS_OFF} $I_{DS} = 1 \text{ mA}$ $V_{DS} = -15 \text{ V};$	V_{GS_OFF} $I_{DS} = 1 \text{ nA}$ $V_{DS} = -15 \text{ V};$	Allocated Test
001	6.57E-12	-3.86E-12	53	5.70	6.90	Control
002	1.02E-10	-5.94E-11	58	4.70	5.90	Bias 1
003	8.04E-11	-4.60E-11	58	4.70	6.40	Bias 1
004	8.58E-11	-4.89E-11	58	4.85	6.10	Bias 1
005	4.43E-11	-2.49E-11	60	4.60	5.90	Bias 2
006	4.48E-11	-2.50E-11	58	5.00	6.50	Bias 2
007	4.78E-11	-2.66E-11	60	4.70	5.90	Bias 2
800	7.71E-11	-4.42E-11	50	6.50	7.70	Bias 3
009	6.52E-11	-3.70E-11	55	5.70	7.10	Bias 3
010	6.05E-12	-3.59E-12	60	4.70	5.80	Control
		R	adiation Level 5,0	00 rd(Si)		
	I_{GS-OFF} $V_{DS} = 0 V;$	I_{DS_OFF} $V_{DS} = -15 \text{ V};$	R_{DS_ON} $I_{DS} = -1 \text{ mA};$	V_{GS_OFF} $I_{DS} = 1 \text{ mA}$	V_{GS_OFF} $I_{DS} = 1 \text{ nA}$	Radiation Sample
S/N	$V_{GS} = 20 \text{ V}$	$V_{GS} = 12 \text{ V}$	$V_{GS} = 0 V$	$V_{DS} = -15 \text{ V};$	$V_{DS} = -15 V;$	Description
001	6.29E-12	-3.67E-12	54	5.70	6.90	Control
002	1.33E-10	-7.52E-11	58	4.70	5.90	Bias 1
003	1.20E-10	-6.77E-11	58	4.70	6.40	Bias 1
004	1.30E-10	-7.36E-11	58	4.85	6.10	Bias 1
005	1.15E-10	-6.58E-11	62	4.60	5.90	Bias 2
006	7.64E-11	-4.17E-11	58	5.00	6.50	Bias 2
007	8.09E-11	-4.43E-11	60	4.70	5.90	Bias 2
800	1.04E-10	-5.85E-11	50	6.50	7.70	Bias 3
009	1.39E-10	-8.04E-11	56	5.70	7.10	Bias 3
010	5.95E-12	-3.52E-12	60	4.70	5.90	Control
		D)00 md(Si)		
	т	1		· · ·	T 7	Radiation
C/N	I_{GS-OFF} $V_{DS} = 0 \text{ V};$ $V_{DS} = 20 \text{ V}$	I_{DS_OFF} $V_{DS} = -15 \text{ V};$ $V_{DS} = -12 \text{ V}$	R_{DS_ON} $I_{DS} = -1 \text{ mA};$ $V = 0 \text{ V}$	V_{GS_OFF} $I_{DS} = 1 \text{ mA}$	V_{GS_OFF} $I_{DS} = 1 \text{ nA}$	Sample
S/N 001	$V_{GS} = 20 \text{ V}$	$V_{GS} = 12 \text{ V}$	$V_{GS} = 0 V$	$V_{DS} = -15 \text{ V};$	$V_{DS} = -15 \text{ V};$	Description
	6.58E-12	-3.85E-12	54	5.70	6.90	Control
002 003	2.02E-10	-1.13E-10 -9.36E-11	58	4.70 4.70	5.90 6.40	Bias 1
003	1.69E-10 1.89E-10	-9.36E-11	58 58	4.70	6.10	Bias 1 Bias 1
004	1.89E-10 1.25E-10	-6.65E-11	60	4.50	5.90	Bias 1
005	1.23E-10 1.23E-10	-6.58E-11	58	5.00	6.50	Bias 2
006	1.23E-10 1.22E-10	-6.49E-11	60	4.70	5.90	Bias 2
007	2.03E-10	-0.49E-11 -1.15E-10	52	6.50	7.70	Bias 2
009	2.01E-10	-1.13E-10	56	5.70	7.10	Bias 3

60

4.70

5.90

Control

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Appendix C. Summary	of Electrical Parameters	After each Radi	iation Level (CONT.)

S/N 001 002 003 004 005 006 007 008 009 010 S/N 001 002	$I_{\text{GS-OFF}} \\ V_{\text{DS}} = 0 \text{ V}; \\ V_{\text{GS}} = 20 \text{ V} \\ 6.79\text{E-}12 \\ 4.81\text{E-}10 \\ 4.64\text{E-}10 \\ 4.81\text{E-}10 \\ 3.84\text{E-}10 \\ 3.56\text{E-}10 \\ 3.47\text{E-}10 \\ 3.85\text{E-}10 \\ 4.18\text{E-}10 \\ 6.80\text{E-}12 \\ \\ I_{\text{GS-OFF}} \\ V_{\text{DS}} = 0 \text{ V}; \\ V_{\text{GS}} = 20 \text{ V}$	I_{DS_OFF} $V_{DS} = -15 \text{ V};$ $V_{GS} = 12 \text{ V}$ $-4.04\text{E}-12$ $-2.73\text{E}-10$ $-2.64\text{E}-10$ $-2.15\text{E}-10$ $-1.97\text{E}-10$ $-1.92\text{E}-10$ $-2.16\text{E}-10$ $-2.37\text{E}-10$ $-4.06\text{E}-12$ Ra I_{DS_OFF} $V_{DS} = -15 \text{ V};$	R _{DS_ON} I _{DS} = -1 mA; V _{GS} = 0 V 54 58 60 60 62 58 60 52 56 60 60 62	$V_{GS_OFF} \\ I_{DS} = 1 \text{ mA} \\ V_{DS} = -15 \text{ V}; \\ 5.70 \\ 4.70 \\ 4.70 \\ 4.90 \\ 4.50 \\ 5.00 \\ 4.70 \\ 6.50 \\ 5.70 \\ 4.70 \\ 6.50 \\ 5.70 \\ 4.70 \\ 6.50 \\ 5.70 \\ 4.70 \\ 6.50 \\ 5.70 \\ 4.70 \\ 6.50 \\ 5.70 \\ 4.70 \\ 6.50 \\ 5.70 \\ 4.70 \\ 6.50 \\ 5.70 \\ 4.70 \\ 6.50 \\ 5.70 \\ 4.70 \\ 6.50 \\ 5.70 \\ 4.70 \\ 6.50 \\ 5.70 \\ 4.70 \\ 6.50 \\ 5.70 \\ 4.70 \\ 6.50 \\ 5.70 \\ 4.70 \\ 6.50 \\ 5.70 \\ 4.70 \\ 6.50 \\ 5.70 \\ 6.50 \\ 5.70 \\ 6.50 \\ 6.50 \\ 5.70 \\ 6.50 \\ 6$	$V_{\text{GS_OFF}}$ $I_{DS} = 1 \text{ nA}$ $V_{DS} = -15 \text{ V};$ 6.90 5.70 6.40 6.10 5.90 6.50 5.90 7.70 7.10 5.90	Allocated Test Control Bias 1 Bias 1 Bias 2 Bias 2 Bias 2 Bias 3 Bias 3 Control
001 002 003 004 005 006 007 008 009 010	$\begin{split} \mathbf{V_{DS}} &= 0 \; \mathbf{V}; \\ \mathbf{V_{GS}} &= 20 \; \mathbf{V} \\ 6.79\text{E-}12 \\ 4.81\text{E-}10 \\ 4.64\text{E-}10 \\ 4.81\text{E-}10 \\ 3.84\text{E-}10 \\ 3.56\text{E-}10 \\ 3.47\text{E-}10 \\ 3.85\text{E-}10 \\ 4.18\text{E-}10 \\ 6.80\text{E-}12 \\ \\ \\ \mathbf{I_{GS-OFF}} \\ \mathbf{V_{DS}} &= 0 \; \mathbf{V}; \end{split}$	$\begin{split} V_{DS} = -15 \ V; \\ V_{GS} = 12 \ V \\ -4.04 E-12 \\ -2.73 E-10 \\ -2.64 E-10 \\ -2.15 E-10 \\ -1.97 E-10 \\ -1.92 E-10 \\ -2.16 E-10 \\ -2.37 E-10 \\ -4.06 E-12 \\ \\ \hline V_{DS} = -15 \ V; \end{split}$	$I_{DS} = -1 \text{ mA};$ $V_{GS} = 0 \text{ V}$ 54 58 60 60 62 58 60 52 56 60	$\begin{split} I_{DS} &= 1 \text{ mA} \\ V_{DS} &= -15 \text{ V}; \\ 5.70 \\ 4.70 \\ 4.70 \\ 4.90 \\ 4.50 \\ 5.00 \\ 4.70 \\ 6.50 \\ 5.70 \\ 4.70 \\ \end{bmatrix}$	$\begin{split} I_{DS} &= 1 \text{ nA} \\ V_{DS} &= -15 \text{ V}; \\ 6.90 \\ 5.70 \\ 6.40 \\ 6.10 \\ 5.90 \\ 6.50 \\ 5.90 \\ 7.70 \\ 7.10 \end{split}$	Control Bias 1 Bias 1 Bias 1 Bias 2 Bias 2 Bias 2 Bias 3 Bias 3
002 003 004 005 006 007 008 009 010 S/N	6.79E-12 4.81E-10 4.64E-10 4.81E-10 3.84E-10 3.56E-10 3.47E-10 3.85E-10 4.18E-10 6.80E-12 I _{GS-OFF} V _{DS} = 0 V;	-4.04E-12 $-2.73E-10$ $-2.64E-10$ $-2.74E-10$ $-2.15E-10$ $-1.97E-10$ $-1.92E-10$ $-2.16E-10$ $-2.37E-10$ $-4.06E-12$ $Rain terms of the second se$	54 58 60 60 62 58 60 52 56 60	5.70 4.70 4.70 4.90 4.50 5.00 4.70 6.50 5.70 4.70	6.90 5.70 6.40 6.10 5.90 6.50 5.90 7.70 7.10	Bias 1 Bias 1 Bias 1 Bias 2 Bias 2 Bias 2 Bias 3 Bias 3
002 003 004 005 006 007 008 009 010 S/N	4.81E-10 4.64E-10 4.81E-10 3.84E-10 3.56E-10 3.47E-10 3.85E-10 4.18E-10 6.80E-12 I _{GS-OFF} V _{DS} = 0 V;	$-2.73\text{E-}10$ $-2.64\text{E-}10$ $-2.74\text{E-}10$ $-2.15\text{E-}10$ $-1.97\text{E-}10$ $-1.92\text{E-}10$ $-2.16\text{E-}10$ $-2.37\text{E-}10$ $-4.06\text{E-}12$ R_{2} I_{DS_OFF} $V_{DS} = -15 \text{ V};$	58 60 60 62 58 60 52 56 60	4.70 4.70 4.90 4.50 5.00 4.70 6.50 5.70 4.70	5.70 6.40 6.10 5.90 6.50 5.90 7.70 7.10	Bias 1 Bias 1 Bias 1 Bias 2 Bias 2 Bias 2 Bias 3 Bias 3
003 004 005 006 007 008 009 010 S/N	$\begin{array}{c} 4.64\text{E-}10 \\ 4.81\text{E-}10 \\ 3.84\text{E-}10 \\ 3.56\text{E-}10 \\ 3.47\text{E-}10 \\ 3.85\text{E-}10 \\ 4.18\text{E-}10 \\ 6.80\text{E-}12 \\ \\ \\ I_{\text{GS-OFF}} \\ V_{\text{DS}} = 0 \text{ V}; \end{array}$	$-2.64E-10$ $-2.74E-10$ $-2.15E-10$ $-1.97E-10$ $-1.92E-10$ $-2.16E-10$ $-2.37E-10$ $-4.06E-12$ Ra I_{DS_OFF} $V_{DS} = -15 \text{ V};$	60 60 62 58 60 52 56 60 adiation Level 30,0	4.70 4.90 4.50 5.00 4.70 6.50 5.70 4.70 00 rd(Si)	6.40 6.10 5.90 6.50 5.90 7.70 7.10	Bias 1 Bias 1 Bias 2 Bias 2 Bias 2 Bias 3 Bias 3
004 005 006 007 008 009 010 S/N	4.81E-10 3.84E-10 3.56E-10 3.47E-10 3.85E-10 4.18E-10 6.80E-12 I _{GS-OFF} V _{DS} = 0 V;	$-2.74E-10$ $-2.15E-10$ $-1.97E-10$ $-1.92E-10$ $-2.16E-10$ $-2.37E-10$ $-4.06E-12$ R_{2} I_{DS_OFF} $V_{DS} = -15 \text{ V};$	60 62 58 60 52 56 60 adiation Level 30,0	4.90 4.50 5.00 4.70 6.50 5.70 4.70	6.10 5.90 6.50 5.90 7.70 7.10	Bias 1 Bias 2 Bias 2 Bias 2 Bias 3 Bias 3
005 006 007 008 009 010 S/N	$3.84\text{E}-10$ $3.56\text{E}-10$ $3.47\text{E}-10$ $3.85\text{E}-10$ $4.18\text{E}-10$ $6.80\text{E}-12$ $I_{\text{GS-OFF}}$ $V_{\text{DS}} = 0 \text{ V};$	$-2.15E-10$ $-1.97E-10$ $-1.92E-10$ $-2.16E-10$ $-2.37E-10$ $-4.06E-12$ R_{2} I_{DS_OFF} $V_{DS} = -15 \text{ V};$	62 58 60 52 56 60 adiation Level 30,0	4.50 5.00 4.70 6.50 5.70 4.70 00 rd(Si)	5.90 6.50 5.90 7.70 7.10	Bias 2 Bias 2 Bias 2 Bias 3 Bias 3
006 007 008 009 010 S/N 001	$3.56E-10$ $3.47E-10$ $3.85E-10$ $4.18E-10$ $6.80E-12$ I_{GS-OFF} $V_{DS} = 0 V;$	$-1.97E-10$ $-1.92E-10$ $-2.16E-10$ $-2.37E-10$ $-4.06E-12$ R_{2} I_{DS_OFF} $V_{DS} = -15 \text{ V};$	58 60 52 56 60 adiation Level 30,0	5.00 4.70 6.50 5.70 4.70 00 rd(Si)	6.50 5.90 7.70 7.10	Bias 2 Bias 2 Bias 3 Bias 3
007 008 009 010 S/N 001	$3.47E-10$ $3.85E-10$ $4.18E-10$ $6.80E-12$ I_{GS-OFF} $V_{DS} = 0 V;$	$-1.92E-10$ $-2.16E-10$ $-2.37E-10$ $-4.06E-12$ R_{2} I_{DS_OFF} $V_{DS}=-15 \text{ V};$	60 52 56 60 adiation Level 30,0	4.70 6.50 5.70 4.70 00 rd(Si)	5.90 7.70 7.10	Bias 2 Bias 3 Bias 3
008 009 010 S/N 001	3.85E-10 4.18E-10 6.80E-12 I_{GS-OFF} $V_{DS} = 0 V;$	$-2.16E-10$ $-2.37E-10$ $-4.06E-12$ R_{i} I_{DS_OFF} $V_{DS}=-15 \text{ V};$	52 56 60 adiation Level 30,0	6.50 5.70 4.70 00 rd(Si)	7.70 7.10	Bias 3 Bias 3
009 010 S/N 001	4.18E-10 6.80E-12 I _{GS-OFF} V _{DS} = 0 V;	$-2.37E-10 \\ -4.06E-12$ R_{a} $I_{DS_OFF} \\ V_{DS} = -15 \text{ V};$	56 60 adiation Level 30,0	5.70 4.70 00 rd(Si)	7.10	Bias 3
S/N 001	6.80E-12 I _{GS-OFF} V _{DS} = 0 V;	-4.06E-12 Ra I _{DS_OFF} V _{DS} = -15 V;	60 adiation Level 30,0	4.70 00 rd(Si)		
S/N 001	I_{GS-OFF} $V_{DS} = 0 V;$	R_{i} I_{DS_OFF} $V_{DS} = -15 \text{ V};$	adiation Level 30,0	00 rd(Si)	0.00	Control
001	$V_{DS} = 0 V;$	I_{DS_OFF} $V_{DS} = -15 \text{ V};$		` '		
001	$V_{DS} = 0 V;$	$V_{DS} = -15 \text{ V};$	R _{DS ON}			
001	$\mathbf{v}_{\mathbf{GS}} = \mathbf{z}\mathbf{v} \mathbf{v}$	X7 10 X7	$I_{DS} = -\bar{1} mA;$	V_{GS_OFF} $I_{DS} = 1 \text{ mA}$	V_{GS_OFF} $I_{DS} = 1 \text{ nA}$	Radiation Sample
	6.04E-12	$V_{GS} = 12 \text{ V}$ -3.55E-12	$V_{GS} = 0 V$	$V_{DS} = -15 \text{ V};$ 5.70	$V_{DS} = -15 \text{ V};$	Description
	6.04E-12 6.26E-10	-3.55E-12 -3.49E-10	54 58	4.65	6.85 5.75	Control
003	5.35E-10	-3.49E-10 -3.01E-10	58	4.05	6.40	Bias 1 Bias 1
004	5.42E-10	-3.04E-10	58	4.75	6.25	Bias 1
005	4.40E-10	-3.04E-10 -2.41E-10	62	4.55	5.85	Bias 1
006	4.20E-10	-2.41E-10 -2.28E-10	58	5.00	6.50	Bias 2
007	4.11E-10	-2.24E-10	60	4.75	6.05	Bias 2
008	5.56E-10	-3.12E-10	52	6.50	7.70	Bias 3
009	5.77E-10	-3.12E-10 -3.24E-10	56	5.75	7.70	Bias 3
010	6.47E-12	-3.82E-12	60	4.65	5.95	Control
010	0.47 E-12	-3.62E-12	00	4.03	5.95	Control
•		Ra	adiation Level 50,0	00 rd(Si)		
201	$I_{GS\text{-}OFF}$ $V_{DS} = 0 \text{ V};$	I_{DS_OFF} $V_{DS} = -15 \text{ V};$	R_{DS_ON} $I_{DS} = -1 \text{ mA};$	V_{GS_OFF} $I_{DS} = 1 \text{ mA}$	V_{GS_OFF} $I_{DS} = 1 \text{ nA}$	Radiation Sample
	- 05		GD	D D /	D 0 /	Description
						Control
						Bias 1
						Bias 1
						Bias 1
						Bias 2
						Bias 2
	Ƙ 35 ⊏ -1∩	-3.45E-10	60	4.75	6.05	Bias 2
007		-4.84E-10	52	6.50	7.75	Bias 3
800	8.67E-10			5.75	7.20	Bias 3
		-5.55E-10 -3.40E-12	56 60	4.65	5.85	Control
S/N 001 002 003 004 005 006		$\begin{split} V_{DS} &= \text{-}15 \text{ V}; \\ V_{GS} &= 12 \text{ V} \\ -3.55 \text{E}\text{-}12 \\ -5.22 \text{E}\text{-}10 \\ -3.92 \text{E}\text{-}10 \\ -4.27 \text{E}\text{-}10 \\ -3.40 \text{E}\text{-}10 \\ -3.66 \text{E}\text{-}10 \end{split}$	$I_{DS} = -1 \text{ mA};$ $V_{GS} = 0 \text{ V}$ 54 58 58 62 58	$I_{DS} = 1 \text{ mA}$ $V_{DS} = -15 \text{ V};$ 5.70 4.65 4.75 4.85 4.55 5.00	$I_{DS} = 1 \text{ nA}$ $V_{DS} = -15 \text{ V};$ 6.85 5.80 6.45 6.25 5.85 6.50	Sa Des C B B B B

-4.08E-12

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6.75E-12

		0Appendix D. Sui	mmary of Electric	cal Tests After An	neal		
Anneal: 156 hours @ 25 °C - (Post-radiation level of 50,000 rd(Si))							
S/N	I_{GS-OFF} $V_{DS} = 0 \text{ V};$ $V_{GS} = 20 \text{ V}$	I_{DS_OFF} $V_{DS} = -15 \text{ V};$ $V_{GS} = 12 \text{ V}$	R_{DS_ON} $I_{DS} = -1 \text{ mA};$ $V_{GS} = 0 \text{ V}$	V_{GS_OFF} $I_{DS} = 1 \text{ mA}$ $V_{DS} = -15 \text{ V};$	$V_{GS_OFF} \\ I_{DS} = 1 \text{ nA} \\ V_{DS} = -15 \text{ V};$	Allocated Test	
001	5.87E-12	-3.43E-12	52.0	5.70	6.95	Control	
002	8.63E-10	-4.97E-10	58.0	4.65	5.85	Bias 1	
003	7.48E-10	-4.31E-10	58.0	4.75	6.45	Bias 1	
004	6.91E-10	-3.96E-10	58.0	4.85	6.25	Bias 1	
005	5.09E-10	-2.81E-10	62.0	4.55	5.85	Bias 2	
006	5.77E-10	-3.23E-10	58.0	5.00	6.50	Bias 2	
007	5.13E-10	-2.84E-10	60.0	4.75	6.05	Bias 2	
800	1.08E-09	-6.16E-10	52.0	6.55	7.75	Bias 3	
009	1.04E-09	-5.84E-10	54.0	5.75	7.20	Bias 3	
010	6.93E-12	-4.17E-12	60.0	4.65	5.95	Control	
	A	anneal: 210 hours @ 2	25 °C - (Post-radia	ation level of 50,00	00 rd(Si))		
S/N	$egin{aligned} \mathbf{I_{GS-OFF}} \ \mathbf{V_{DS}} &= 0 \ \mathbf{V}; \ \mathbf{V_{GS}} &= 20 \ \mathbf{V} \end{aligned}$	I_{DS_OFF} $V_{DS} = -15 \text{ V};$ $V_{GS} = 12 \text{ V}$	R_{DS_ON} $I_{DS} = -1 \text{ mA};$ $V_{GS} = 0 \text{ V}$	$V_{GS_OFF} \\ I_{DS} = 1 \text{ mA} \\ V_{DS} = -15 \text{ V};$	V_{GS_OFF} $I_{DS} = 1 \text{ nA}$ $V_{DS} = -15 \text{ V};$	Allocated Test	
001	8.08E-12	-4.97E-12	54.0	5.70	6.85	Control	
002	9.24E-10	-5.35E-10	58.0	4.65	5.85	Bias 1	
003	7.00E-10	-4.00E-10	58.0	4.75	6.45	Bias 1	
004	7.34E-10	-4.23E-10	58.0	4.85	6.25	Bias 1	
005	5.54E-10	-3.10E-10	62.0	4.55	5.85	Bias 2	
006	5.34E-10	-2.98E-10	58.0	5.00	6.50	Bias 2	
007	5.32E-10	-2.97E-10	60.0	4.75	6.05	Bias 2	
800	1.06E-09	-6.00E-10	52.0	6.55	7.85	Bias 3	
009	1.07E-09	-6.01E-10	56.0	5.75	7.20	Bias 3	

60.0

4.65

5.95

Control

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Appendix E. Graphical Summary of Electrical Tests Results

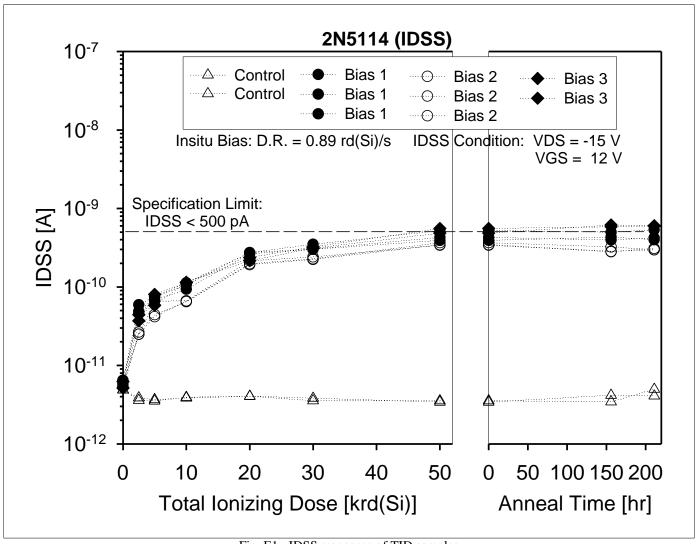


Fig. E1: IDSS responses of TID samples

Appendix E. Graphical Summary Continued

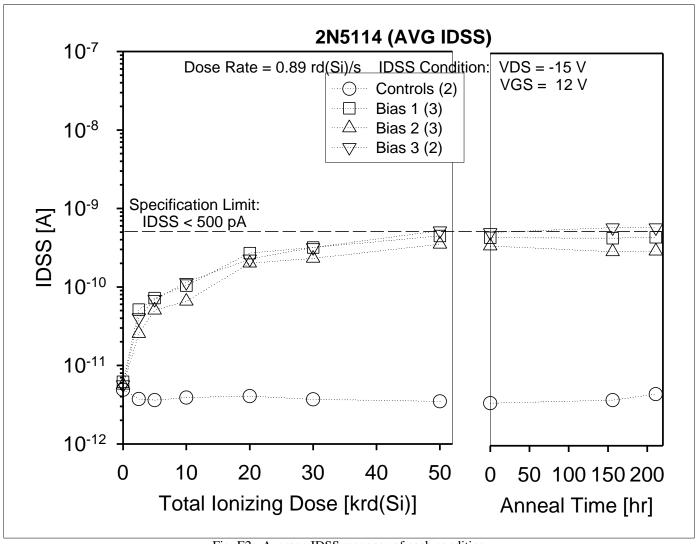


Fig. E2: Average IDSS response of each condition

Appendix E. Graphical Summary Continued

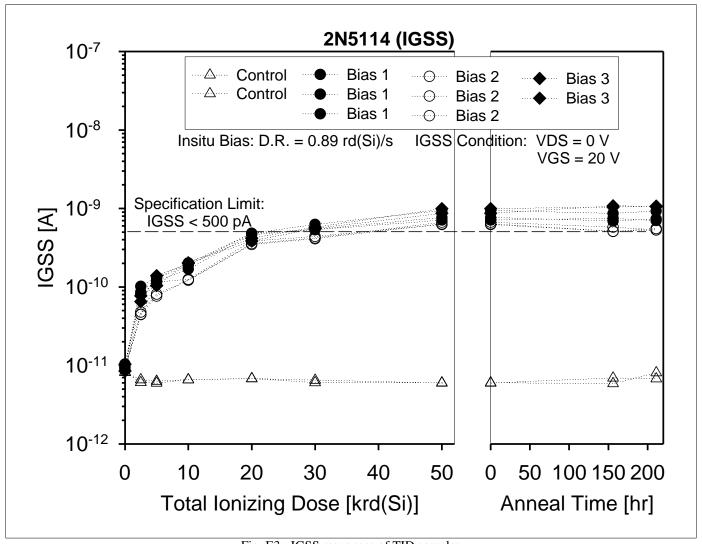


Fig. E3: IGSS responses of TID samples

Appendix E. Graphical Summary Continued

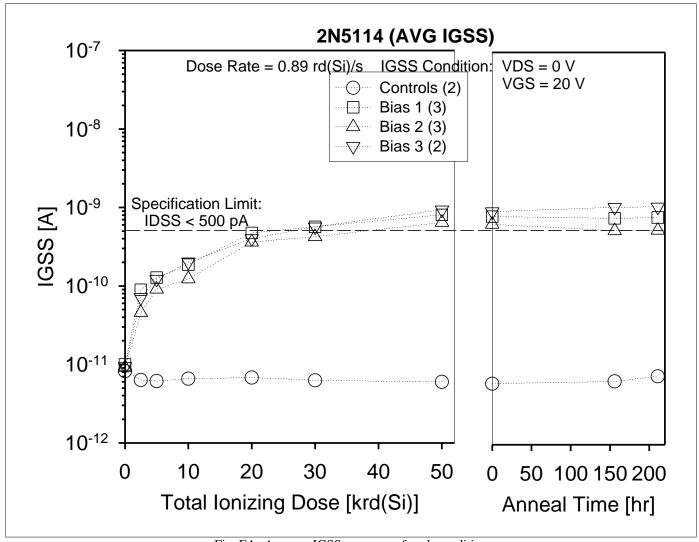


Fig. E4: Average IGSS response of each condition

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Appendix E. Graphical Summary Continued

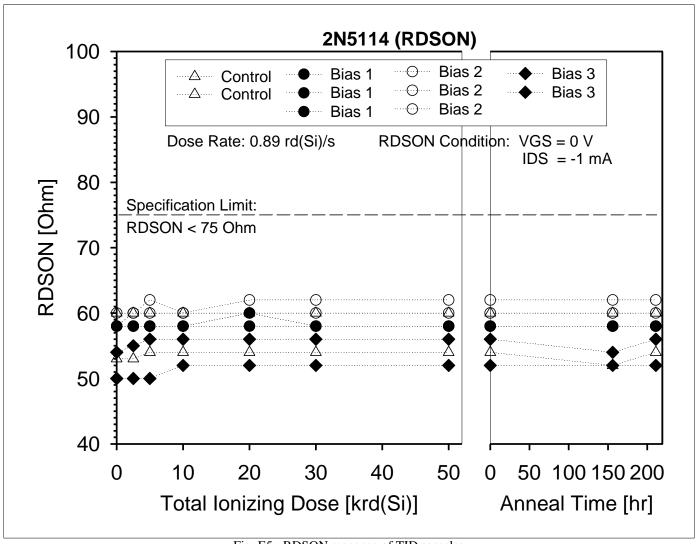


Fig. E5: RDSON response of TID samples

Appendix E. Graphical Summary Continued

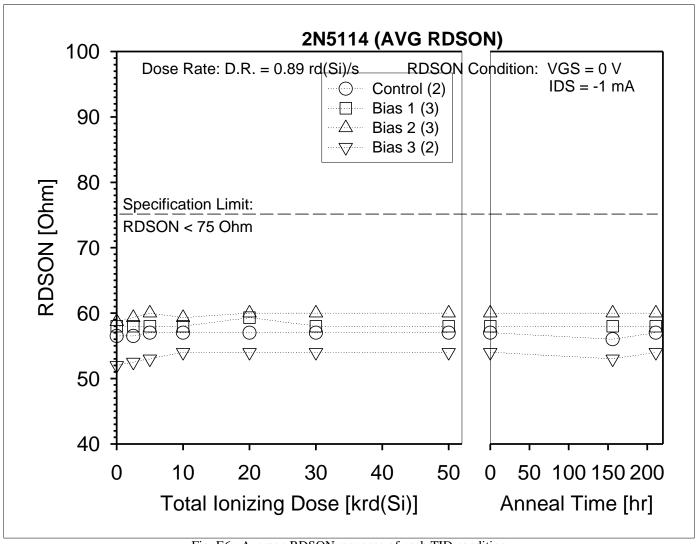


Fig. E6: Average RDSON response of each TID condition

Appendix E. Graphical Summary Continued

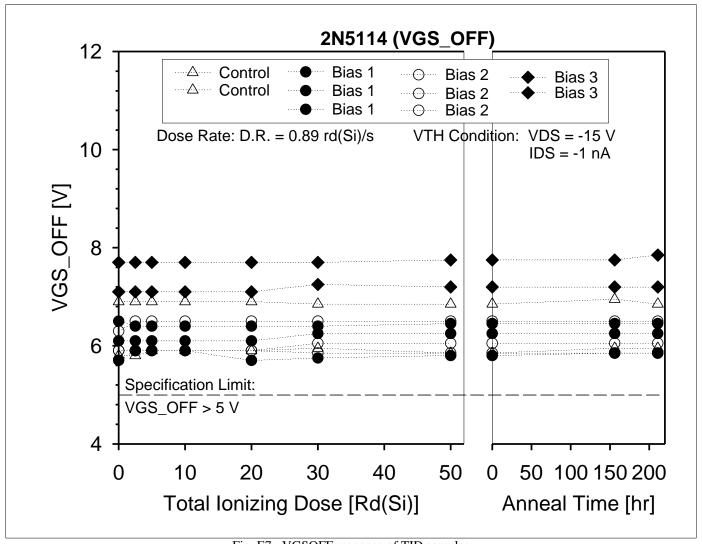


Fig. E7: VGSOFF response of TID samples

Appendix E. Graphical Summary Continued

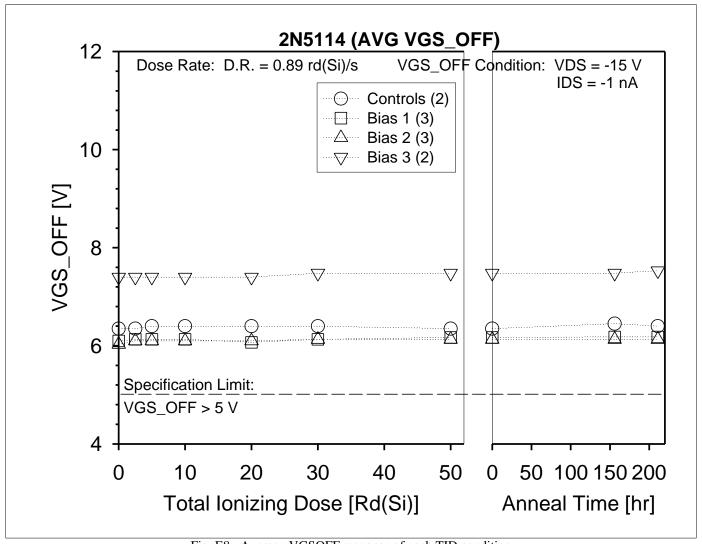


Fig. E8: Average VGSOFF response of each TID condition